# **REMARKS**

Claims 1-40 are canceled, leaving claims 41-47 pending in the application.

Applicant requests substantive examination of pending claims 41-47

Respectfully submitted,

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### IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

priority Application Serial No
priority Filing Date August 7, 2000
Inventor Gurtej S. Sandhu et al.
Assignee Micron Technology, Inc.
priority Group Art Unit
priority Examiner Laura M. Schillinger
Attorney's Docket No MI22-1898
Title: Transistor Structures

# VERSION WITH MARKINGS TO SHOW CHANGES MADE ACCOMPANYING PRELIMINARY AMENDMENT

## In the Specification

The replacement specification paragraphs incorporate the following amendments. <u>Underlines</u> indicate insertions and <del>strikeouts</del> indicate deletions.

The title is amended as follows: Transistor Structures, Methods of Incorporating Nitrogen into Silicon-Oxide-Containing Layers; and Methods of Forming Transistors

The following is inserted on p. 1 before the "Technical Field" section,

### CROSS REFERENCE TO RELATED APPLICATION

This patent resulted from a divisional application of U.S. Patent Application

Serial No. 09/633,556, which was filed on August 7, 2000.

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